

深圳市晶泰源电子有限公司

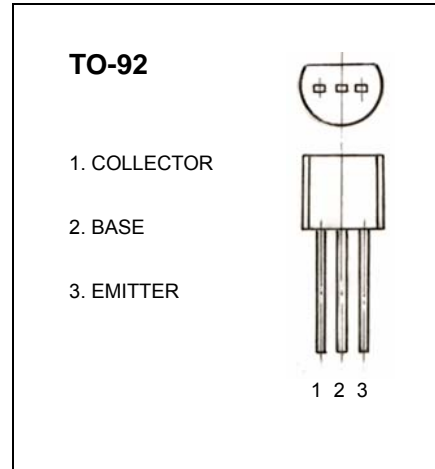
BC556/BC557/BC558 TRANSISTOR (PNP)

FEATURES

- High Voltage
- Complement to BC546/BC547/BC548

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	BC556 -80 BC557 -50 BC558 -30	V
	V_{CEO}	Collector-Emitter Voltage	-65
			-45
-30			
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-100	mA
P_C	Collector Power Dissipation	625	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V_{CBO}	$I_C = -100\mu\text{A}, I_E = 0$	BC556 -80			V
			BC557 -50			
			BC558 -30			
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -2\text{mA}, I_B = 0$	BC556 -65			V
			BC557 -45			
			BC558 -30			
Emitter-base breakdown voltage	V_{EBO}	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -70\text{V}, I_E = 0$ $V_{CB} = -45\text{V}, I_E = 0$ $V_{CB} = -25\text{V}, I_E = 0$	BC556 -0.1			μA
			BC557 -0.1			
			BC558 -0.1			
Collector cut-off current	I_{CEO}	$V_{CE} = -60\text{V}, I_B = 0$ $V_{CE} = -40\text{V}, I_B = 0$ $V_{CE} = -25\text{V}, I_B = 0$	BC556 -0.1			μA
			BC557 -0.1			
			BC558 -0.1			
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	BC556 120		800	
			BC557 120		800	
			BC558 120		800	
			BC557A 120		220	
			BC556B/BC557B/BC558B 180		460	
			BC557C 420		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -5\text{mA}$			-0.65	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100\text{mA}, I_B = -5\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$ $f = 100\text{MHz}$	150			MHz